**Product data sheet** 

## 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol                                  | Parameter                        | Conditions                                       |     | Min | Тур | Max | Unit |
|---|----------------------------------|--|-----|-----|-----|-----|------|
| Per transistor                          |                                  |  |     |     |     |     |      |
| $V_{DS}$                                | drain-source voltage             | T <sub>j</sub> = 25 °C                           |     | -   | -   | 60  | V    |
| $V_{GS}$                                | gate-source voltage              |  |     | -20 | -   | 20  | V    |
| I <sub>D</sub>                          | drain current                    | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C | [1] | -   | -   | 170 | mA   |
| Static characteristics (per transistor) |                                  |  |     |     |     |     |      |
| R <sub>DSon</sub>                       | drain-source on-state resistance | $V_{GS}$ = 10 V; $I_D$ = 170 mA; $T_j$ = 25 °C   |     | -   | 3   | 4.5 | Ω    |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



60 V, dual N-channel Trench MOSFET

# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol  |
|-----|--------|-------------|--------------------|-----------------|
| 1   | S1     | source TR1  | □6 □5 □4           | D1 D2           |
| 2   | G1     | gate TR1    |                    |                 |
| 3   | D2     | drain TR2   | 0                  | G1 $G2$ $G2$    |
| 4   | S2     | source TR2  | ☐1 ☐2 ☐3           |                 |
| 5   | G2     | gate TR2    | TSSOP6 (SOT363)    |                 |
| 6   | D1     | drain TR1   |                    | S1 S2 017aaa256 |

# 6. Ordering information

Table 3. Ordering information

| Type number | Package |  |         |  |  |  |
|-------------|---------|--|---------|--|--|--|
|             | Name    | Description                              | Version |  |  |  |
| NX138AKS    | TSSOP6  | plastic surface-mounted package; 6 leads | SOT363  |  |  |  |

# 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
|             | [1]          |
| NX138AKS    | F8%          |

[1] % = placeholder for manufacturing site code

60 V, dual N-channel Trench MOSFET

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions  |     | Min | Max  | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| Per transis      | stor                    |   |     |     |      |      |
| $V_{DS}$         | drain-source voltage    | T <sub>j</sub> = 25 °C                              |     | -   | 60   | V    |
| $V_{GS}$         | gate-source voltage     |   |     | -20 | 20   | V    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C    | [1] | -   | 170  | mA   |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C   | [1] | -   | 110  | mA   |
| I <sub>DM</sub>  | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$ |     | -   | 680  | mA   |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> = 25 °C                            | [2] | -   | 265  | mW   |
|                  |                         |   | [1] | -   | 325  | mW   |
|                  |                         | T <sub>sp</sub> = 25 °C                             |     | -   | 1.33 | W    |
| Per device       |                         |   | '   |     |      | ,    |
| T <sub>j</sub>   | junction temperature    |   |     | -55 | 150  | °C   |
| T <sub>amb</sub> | ambient temperature     |   |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature     |   |     | -65 | 150  | °C   |
| Source-dra       | ain diode               | ,   | 1   |     | -    |      |
| I <sub>S</sub>   | source current          | T <sub>amb</sub> = 25 °C                            | [1] | -   | 170  | mA   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### 60 V, dual N-channel Trench MOSFET

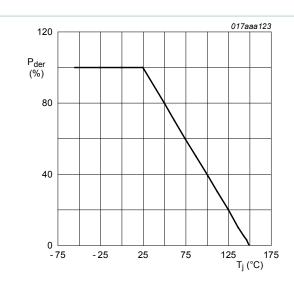


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

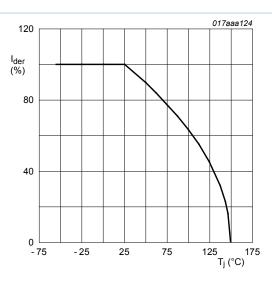
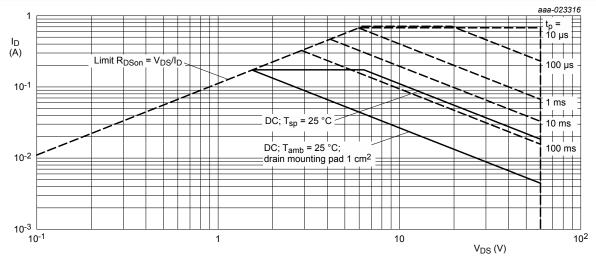


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



I<sub>DM</sub> = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

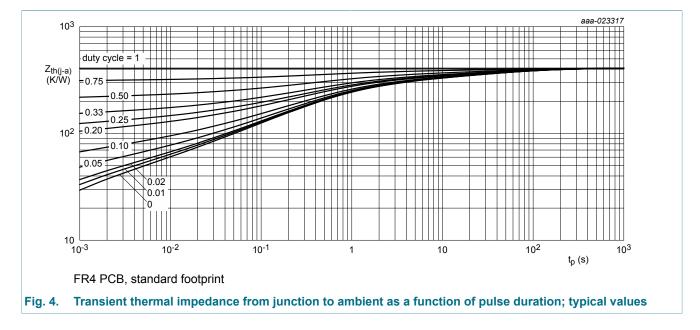
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### 9. Thermal characteristics

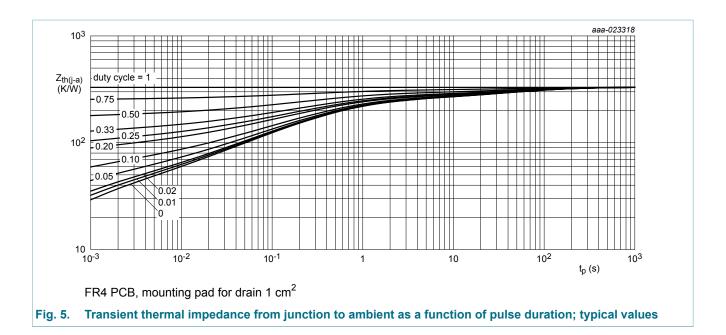
Table 6. Thermal characteristics

| Symbol   | Parameter  | Conditions |     | Min | Тур | Max | Unit |  |
|--|--|------------|-----|-----|-----|-----|------|--|
| Per transistor   |  |            |     |     |     |     |      |  |
| R <sub>th(j-a)</sub> thermal resistance from junction to ambient |  | _          | [1] | -   | 500 | 560 | K/W  |  |
|  |  |            | [2] | -   | 450 | 480 | K/W  |  |
| R <sub>th(j-sp)</sub>  | thermal resistance from junction to solder point |            |     | -   | 100 | 115 | K/W  |  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



### **60 V, dual N-channel Trench MOSFET**



**60 V, dual N-channel Trench MOSFET** 

## 10. Characteristics

Table 7 Characteristics

| Symbol              | Parameter                         | Conditions   | Min | Тур | Max  | Unit |
|---------------------|-----------------------------------|--|-----|-----|------|------|
| Static chara        | acteristics (per transistor)      |  | '   |     |      |      |
| $V_{(BR)DSS}$       | drain-source<br>breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$                             | 60  | -   | -    | V    |
| $V_{GSth}$          | gate-source threshold voltage     | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                  | 0.8 | 1.1 | 1.5  | V    |
| I <sub>DSS</sub>    | drain leakage current             | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -   | -   | 1    | μA   |
| I <sub>GSS</sub>    | gate leakage current              | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -   | -   | 2    | μA   |
|                     |                                   | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | -   | -2   | μA   |
|                     |                                   | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -   | -   | 0.5  | μA   |
|                     |                                   | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | -   | -0.5 | μA   |
|                     |                                   | V <sub>GS</sub> = 5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C     | -   | -   | 100  | nA   |
|                     |                                   | V <sub>GS</sub> = -5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -   | -   | -100 | nA   |
| R <sub>DSon</sub>   | drain-source on-state resistance  | $V_{GS}$ = 10 V; $I_D$ = 170 mA; $T_j$ = 25 °C                           | -   | 3   | 4.5  | Ω    |
|                     |                                   | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 170 mA; T <sub>j</sub> = 150 °C | -   | 6   | 9    | Ω    |
|                     |                                   | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 150 mA; T <sub>j</sub> = 25 °C   | -   | 3.7 | 5.2  | Ω    |
|                     |                                   | V <sub>GS</sub> = 4 V; I <sub>D</sub> = 130 mA; T <sub>j</sub> = 25 °C   | -   | 4   | 6.3  | Ω    |
|                     |                                   | $V_{GS}$ = 2.5 V; $I_D$ = 100 A; $T_j$ = 25 °C                           | -   | 5   | 10   | Ω    |
| 9fs                 | forward transconductance          | $V_{DS}$ = 10 V; $I_D$ = 170 mA; $T_j$ = 25 °C                           | -   | 3.5 | -    | S    |
| Dynamic ch          | naracteristics (per transist      | or)  | ·   |     |      |      |
| Q <sub>G(tot)</sub> | total gate charge                 | $V_{DS}$ = 30 V; $I_{D}$ = 170 mA; $V_{GS}$ = 10 V;                      | -   | 0.9 | 1.4  | nC   |
| $Q_{GS}$            | gate-source charge                | T <sub>j</sub> = 25 °C   | -   | 0.1 | -    | nC   |
| $Q_{GD}$            | gate-drain charge                 |  | -   | 0.2 | -    | nC   |
| C <sub>iss</sub>    | input capacitance                 | $V_{DS} = 30 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$        | -   | 15  | 20   | pF   |
| C <sub>oss</sub>    | output capacitance                | T <sub>j</sub> = 25 °C   | -   | 2.3 | -    | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance      |  | -   | 1.5 | -    | pF   |
| t <sub>d(on)</sub>  | turn-on delay time                | $V_{DS}$ = 30 V; $I_{D}$ = 170 mA; $V_{GS}$ = 10 V;                      | -   | 8   | 12   | ns   |
| t <sub>r</sub>      | rise time                         | $R_{G(ext)} = 75 \Omega; T_j = 25 °C$                                    | -   | 10  | -    | ns   |
| t <sub>d(off)</sub> | turn-off delay time               |  | -   | 8   | 20   | ns   |
| t <sub>f</sub>      | fall time                         |  | -   | 5   | -    | ns   |
| Source-drai         | in diode (per transistor)         |  | ·   |     | ·    |      |
| $V_{SD}$            | source-drain voltage              | $I_S$ = 170 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C                            | -   | 8.0 | 1.2  | V    |
|                     |                                   |  |     |     |      |      |

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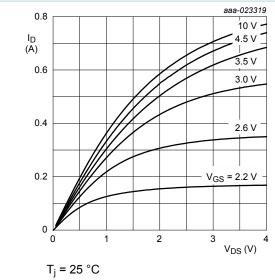


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

2.6 V

0.2

 $T_i = 25 \,^{\circ}C$ 

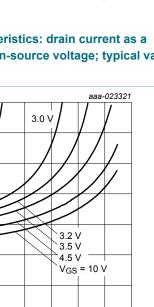


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

0.4

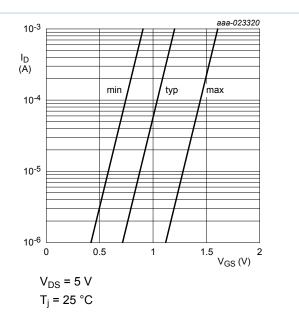


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

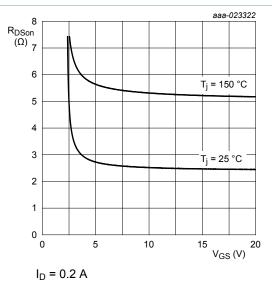


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

R<sub>DSon</sub> (Ω)

6

5

4

3

2

### 60 V, dual N-channel Trench MOSFET

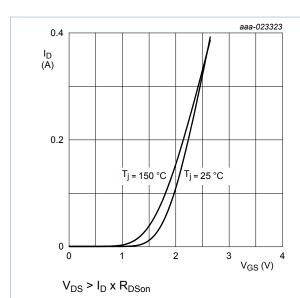


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

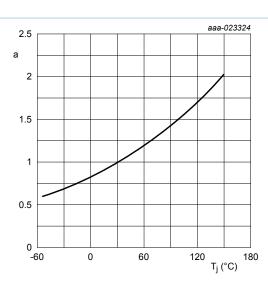


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

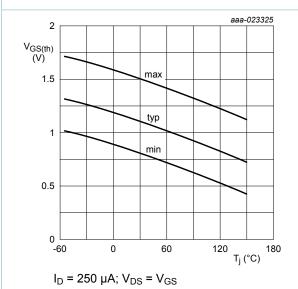


Fig. 12. Gate-source threshold voltage as a function of junction temperature

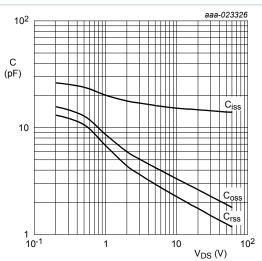


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

 $f = 1 MHz; V_{GS} = 0 V$ 

#### 60 V, dual N-channel Trench MOSFET

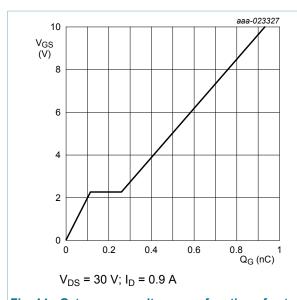


Fig. 14. Gate-source voltage as a function of gate charge; typical values

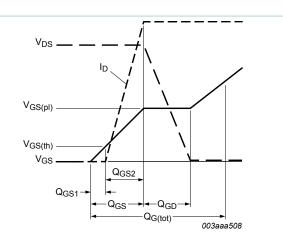


Fig. 15. MOSFET transistor: Gate charge waveform definitions

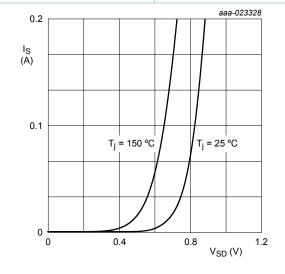
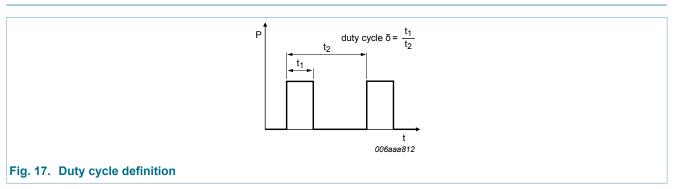


Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information

 $V_{GS} = 0 V$ 



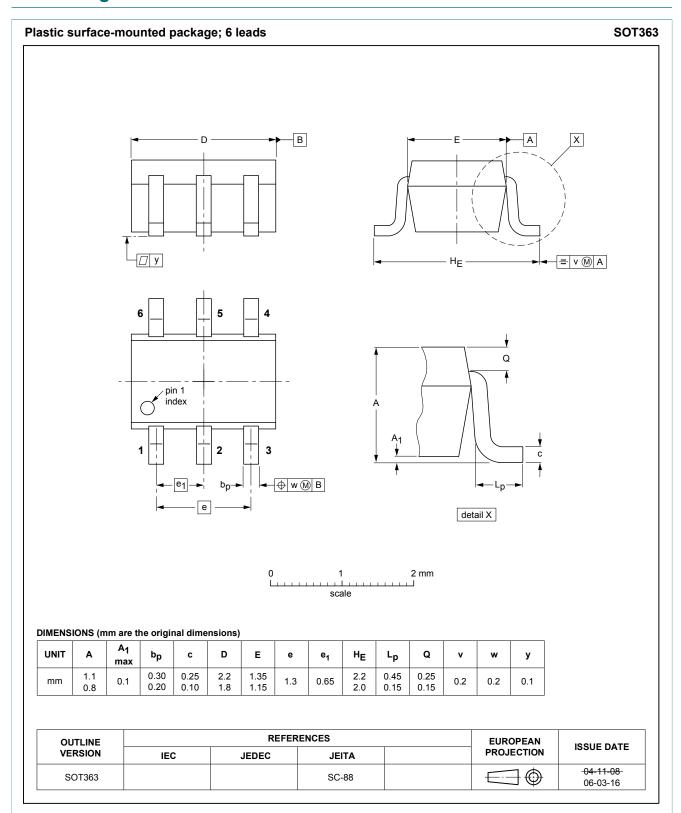
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## 12. Package outline

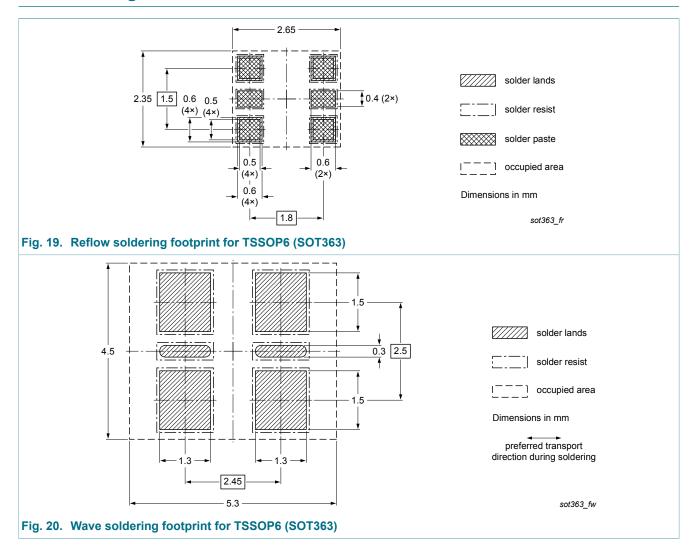


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# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| NX138AKS v.1  | 20160615     | Product data sheet | -             | -          |

#### 60 V, dual N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary<br>[short] data<br>sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product<br>[short] data<br>sheet     | Production         | This document contains the product specification.                                     |

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### **60 V, dual N-channel Trench MOSFET**

### 16. Contents

| 1    | General description     | 1  |
|------|-------------------------|----|
| 2    | Features and benefits   | 1  |
| 3    | Applications            | 1  |
| 4    | Quick reference data    | 1  |
| 5    | Pinning information     | 2  |
| 6    | Ordering information    | 2  |
| 7    | Marking                 | 2  |
| 8    | Limiting values         | 3  |
| 9    | Thermal characteristics | 5  |
| 10   | Characteristics         | 7  |
| 11   | Test information        | 10 |
| 12   | Package outline         | 11 |
| 13   | Soldering               | 12 |
| 14   | Revision history        | 13 |
| 15   | Legal information       | 14 |
| 15.1 | Data sheet status       | 14 |
| 15.2 | Definitions             | 14 |
| 15.3 | Disclaimers             | 14 |
| 15.4 | Trademarks              | 15 |

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